P6MNC4P2

30V Dual N-Channel MOSFETs

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

	BV_{DSS}	$R_{DS(ON)}$	I_D
Q1	30 V	9.5 mΩ	43 A
Q2	30 V	4.2 mΩ	85 A

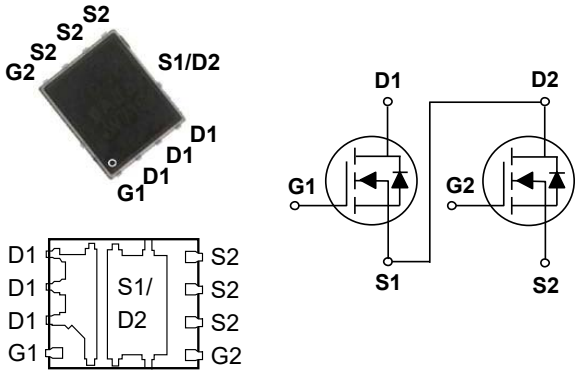
Features

- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- MB / VGA / Vcore
- POL Buck Applications
- SMPS 2nd SR

PPAK5x6 Asymmetric Dual Pin Configuration



Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
V_{DS}	Drain-Source Voltage	30	30	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D	Drain Current - Continuous (T_C=25°C)	43	85	A
	Drain Current - Continuous (T_C=100°C)	27.2	54	A
I_{DM}	Drain Current - Pulsed (NOTE 1), Chip/Package Limit	172	340	A
EAS	Single Pulse Avalanche Energy (NOTE 2)	45	88	mJ
IAS	Single Pulse Avalanched Current (NOTE 2)	30	42	A
P_D	Power Dissipation (T_C=25°C)	27.2	48	W
	Power Dissipation - Derate above 25°C	0.22	0.38	W/°C
T_J	Operating Junction Temperature Range	-55 to 150		°C
T_{STG}	Storage Temperature Range	-55 to 150		°C
Marking Code		NC4P2		

Thermal Characteristics

Symbol		Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Q1	Thermal Resistance Junction to Ambient	---	62	°C/W
	Q2		---	62	°C/W
$R_{\theta JC}$	Q1	Thermal Resistance Junction to Case	---	4.6	°C/W
	Q2		---	2.6	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	Q1	30	---	---	V
			Q2	30	---	---	
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25°C	Q1	---	---	1	uA
			Q2	---	---	1	
		V_{DS}=24V , V_{GS}=0V , T_J=125°C	Q1	---	---	10	uA
			Q2	---	---	10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	Q1	---	---	±100	nA
			Q2	---	---	±100	

On Characteristics

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance (NOTE 3)	V_{GS}=10V , I_D=8A	Q1	---	7.5	9.5	mΩ
		V_{GS}=10V , I_D=20A	Q2	---	3.3	4.2	
		V_{GS}=4.5V , I_D=5A	Q1	---	11	14.5	
		V_{GS}=4.5V , I_D=10A	Q2	---	4.5	6	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250uA	Q1	1.0	1.6	2.5	V
			Q2	1.0	1.6	2.5	
gfs	Forward Transconductance	V_{DS}=10V , I_D=8A	Q1	---	9.5	---	S
		V_{DS}=10V , I_D=10A	Q2	---	15.5	---	

Dynamic and switching Characteristics

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{DS}=15V , V_{GS}=4.5V , I_D=10A (NOTE 3、4)	Q1	---	7.5	12	nC
			Q2	---	24	34	
Q_{gs}	Gate-Source Charge		Q1	---	1.3	2.6	
			Q2	---	4.2	6	
Q_{gd}	Gate-Drain Charge		Q1	---	4.5	8	
			Q2	---	13	18	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω , I_D=8A (NOTE 3、4)	Q1	---	4.8	9	nS
			Q2	---	12.6	24	
T_r	Rise Time		Q1	---	12.5	24	
			Q2	---	19.5	37	
$T_{d(off)}$	Turn-Off Delay Time		Q1	---	27.6	52	
			Q2	---	42.8	81	
T_f	Fall Time		Q1	---	8.2	16	
			Q2	---	13.2	25	

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Dynamic and switching Characteristics

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	Q1	---	680	1000	pF
			Q2	---	2200	3190	
C_{oss}	Output Capacitance		Q1	---	150	220	
			Q2	---	280	405	
C_{rss}	Reverse Transfer Capacitance		Q1	---	70	105	
			Q2	---	177	255	
Rg	Gate resistance	V_{GS}=0V , V_{DS}=0V , F=1MHz	Q1	---	2.7	5.4	Ω
			Q2	---	2	4	

Guaranteed Avalanche Energy

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	V_{DD}=25V , L=0.1mH , IAS=10A	Q1	5	---	---	mJ
		V_{DD}=25V , L=0.1mH , IAS=20A	Q2	20	---	---	

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	Q1	---	---	43	A
			Q2	---	---	85	
I_{SM}	Pulsed Source Current (NOTE 3)		Q1	---	---	86	A
			Q2	---	---	170	
V_{SD}	Diode Forward Voltage (NOTE 3)	V_{GS}=0V , I_S=1A , T_J=25°C	Q1	---	---	1	V
			Q2	---	---	1	

NOTES：

1. Repetitive Rating：Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, Q1：I_{AS}=30A, Q2：IAS=42A R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

Characteristics Curves

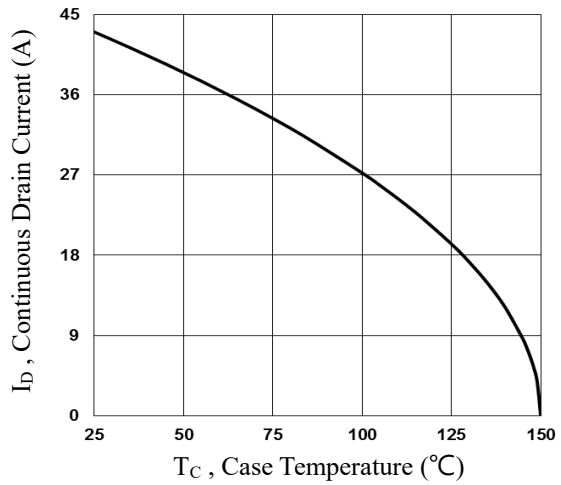


Fig.1 Q1 Continuous Drain Current vs. T_C

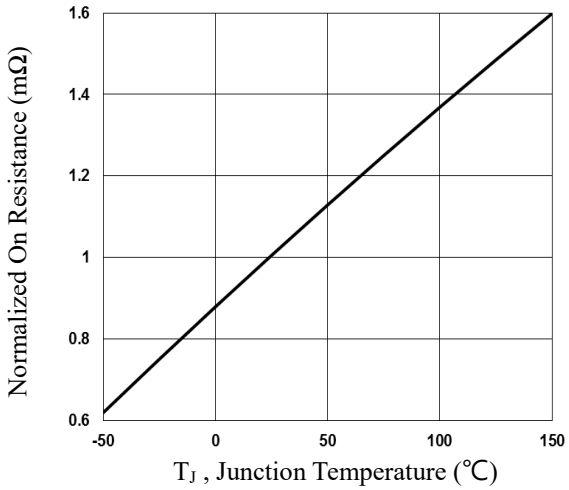


Fig.2 Q1 Normalized RDSON vs. T_J

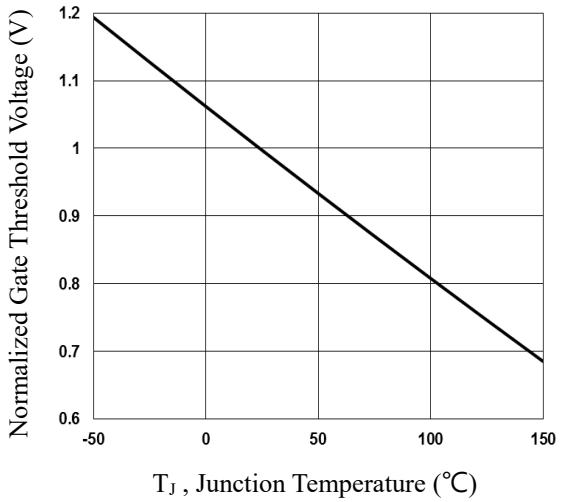


Fig.3 Q1 Normalized V_{th} vs. T_J

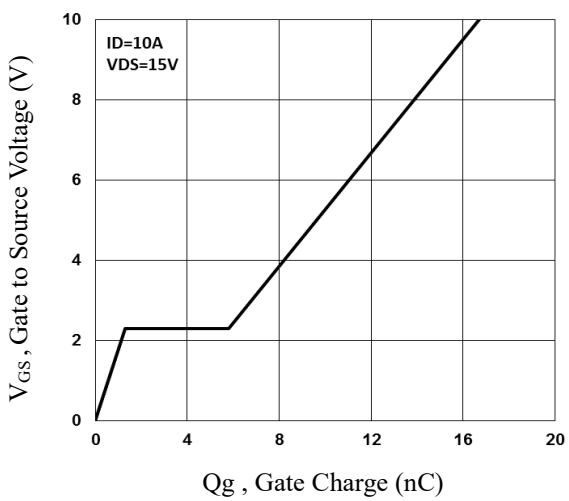


Fig.4 Q1 Gate Charge Waveform

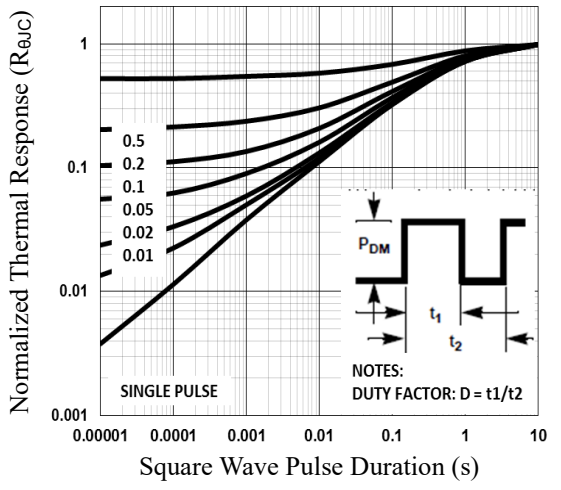


Fig.5 Q1 Normalized Transient Impedance

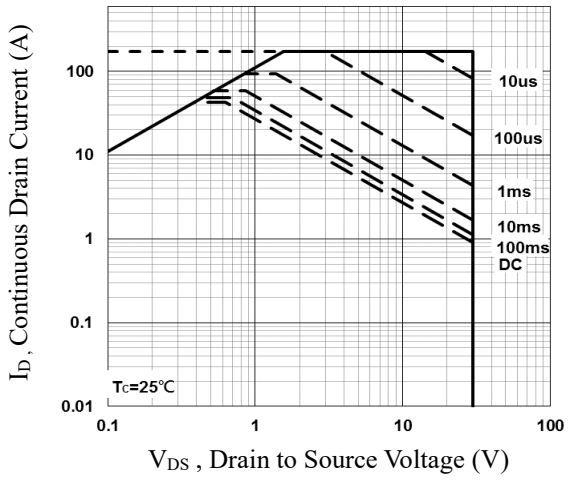


Fig.6 Q1 Maximum Safe Operation Area

Characteristics Curves

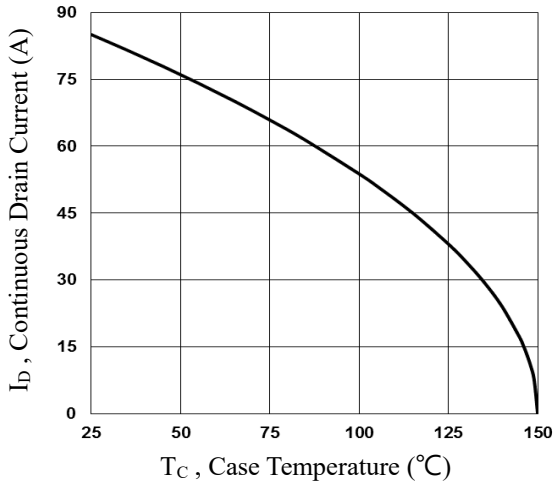


Fig.7 Q2 Continuous Drain Current vs. T_C

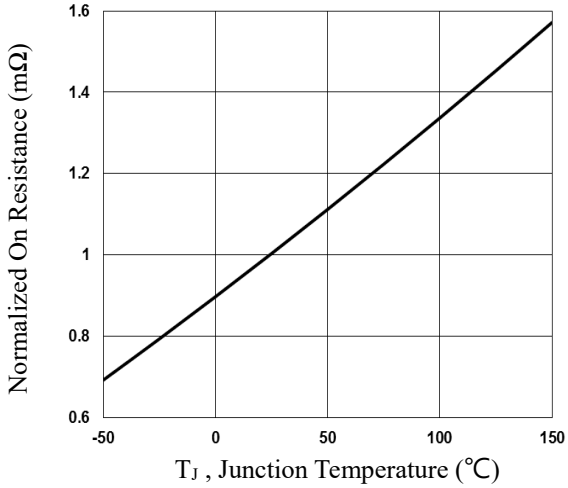


Fig.8 Q2 Normalized RDSON vs. T_J

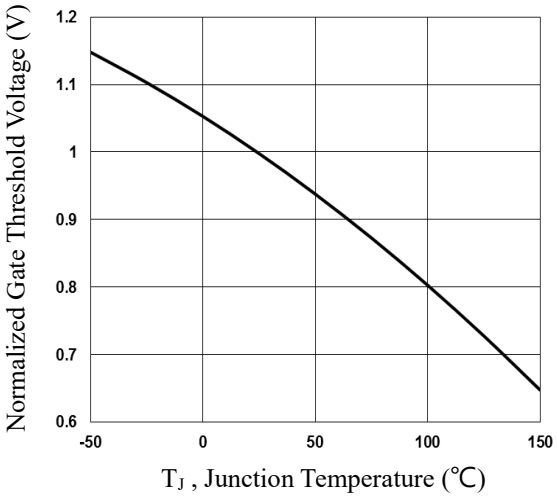


Fig.9 Q2 Normalized V_{th} vs. T_J

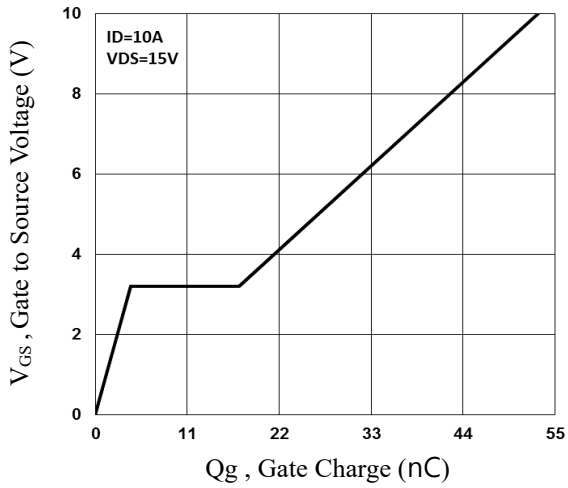


Fig.10 Q2 Gate Charge Waveform

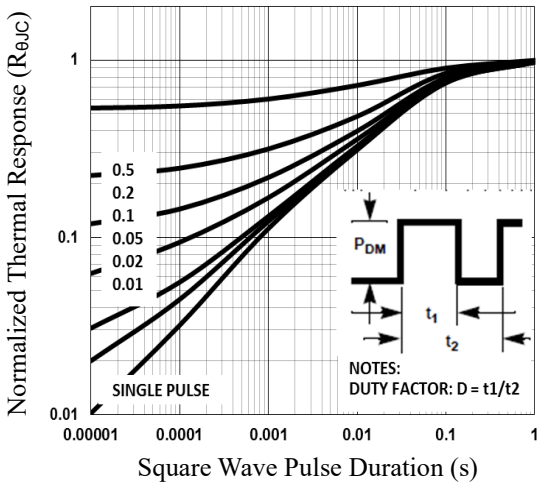


Fig.11 Q2 Normalized Transient Impedance

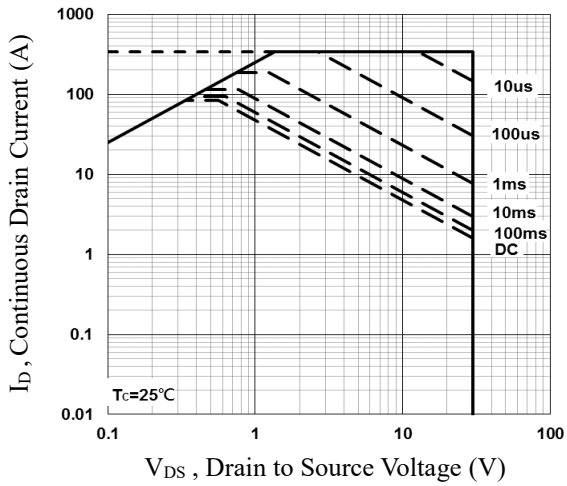


Fig.12 Q2 Maximum Safe Operation Area

Characteristics Curves

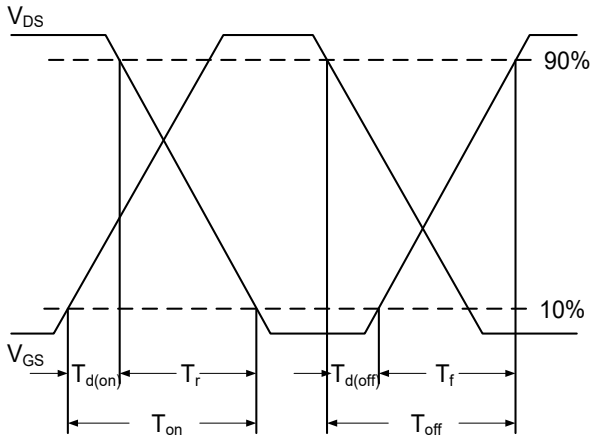
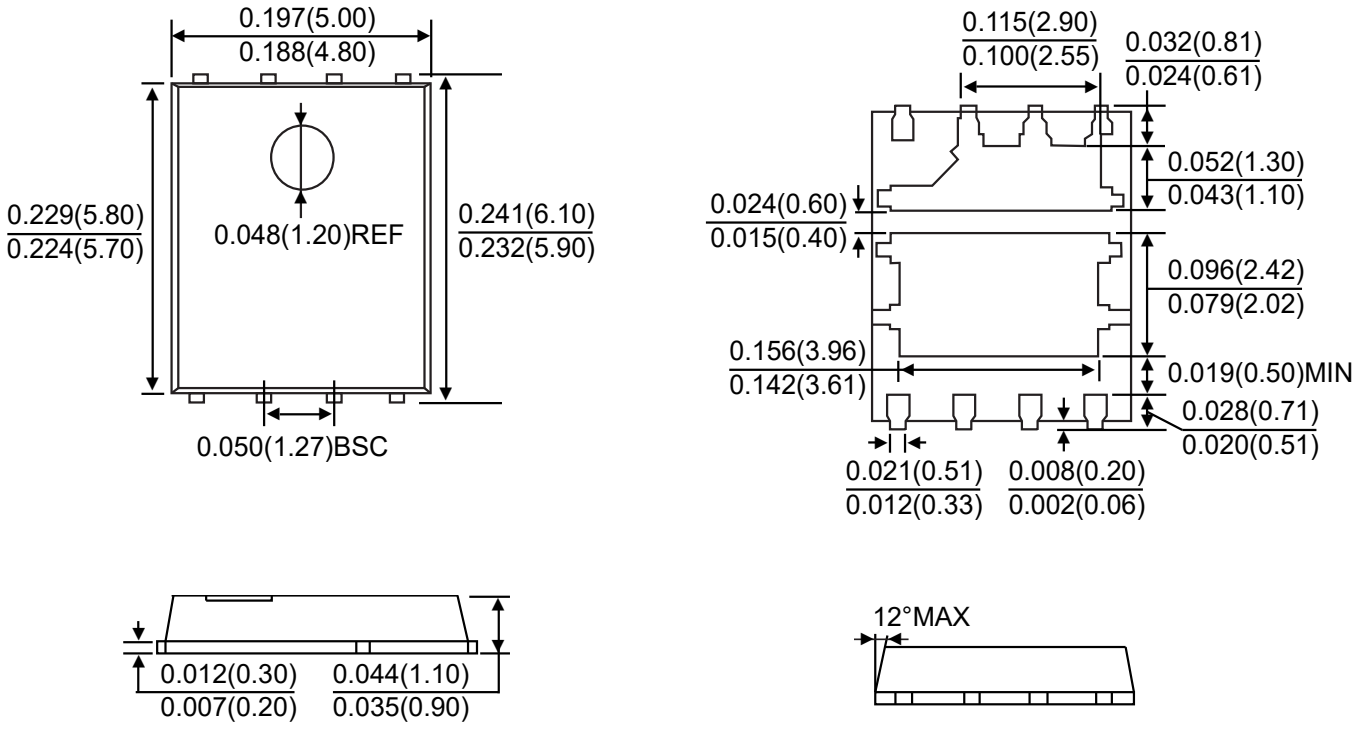


Fig.13 Switching Time Waveform

Package Outline Dimensions



PPAK5x6 Asymmetric Dual

Dimensions in inches and (millimeters)

LEGAL DISCLAIMER

- The product is provided “AS IS” without any guarantees or warranty. In association with the product, Eris Technology Corporation, its affiliates, and their directors, officers, employees, agents, successors and assigns (collectively, the “Eris”) makes no warranties of any kind, either express or implied, including but not limited to warranties of merchantability, fitness for a particular purpose, of title, or of non-infringement of third party rights.
- The information in this document and any product described herein are subject to change without notice and should not be construed as a commitment by Eris. Eris assumes no responsibility for any errors that may appear in this document.
- Eris does not assume any liability arising out of the application or use of this document or any product described herein, any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Eris and all the companies whose products are represented on Eris website, harmless against all damages.
- No license, express or implied, by estoppels or otherwise, to any intellectual property is granted by this document or by any conduct of Eris. Product name and markings notes herein may be trademarks of their respective owners.
- Eris does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- Should Customers purchase or use Eris products for any unintended or unauthorized application, Customers shall indemnify and hold Eris and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.
- The official text is written in English and the English version of this document is the only version endorsed by Eris. Any discrepancies or differences created in the translations are not binding and have no legal effect on Eris for compliance or enforcement purposes.